MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MC54/74HC367

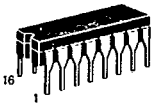
Hex 3-State Noninverting Buffer with Separate 2-Bit and 4-Bit Sections

High-Performance Silicon-Gate CMOS

The MC54/74HC367 is identical in pinout to the LS367. The device inputs are compatible with standard CMOS outputs, with pullup resistors, they are compatible with LSTTL outputs.

This device is arranged into 2-bit and 4-bit sections, each having its own active-low Output Enable. When either of the enables is high, the affected buffer outputs are placed into high-impedance states. The HC367 has noninverting outputs.

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 92 FETs or 23 Equivalent Gates



J SUFFIX
CERAMIC
CASE 620-09

N SUFFIX
PLASTIC
CASE 648-06

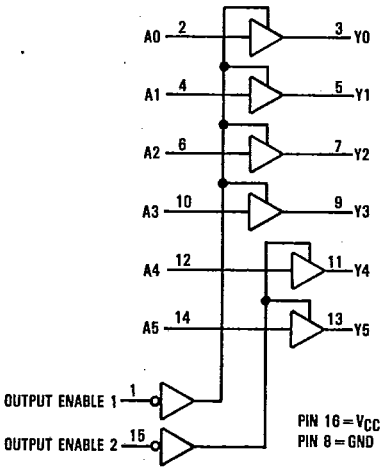
D SUFFIX
SOIC
CASE 751B-03

ORDERING INFORMATION

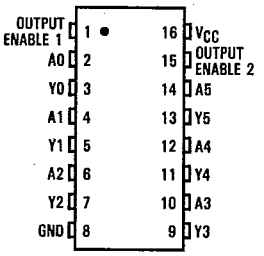
MC74HCXXXN	Plastic
MC54HCXXXJ	Ceramic
MC74HCXXXD	SOIC

T_A = −55° to 125°C for all packages.
Dimensions in Chapter 7.

LOGIC DIAGRAM



PIN ASSIGNMENT



FUNCTION TABLE

Inputs		Output
Enable 1, Enable 2	A	Y
L	L	L
L	H	H
H	X	Z

X = don't care
Z = high-impedance

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MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	−0.5 to +7.0	V
V_{in}	DC Input Voltage (Referenced to GND)	−1.5 to V_{CC}+1.5	V
V_{out}	DC Output Voltage (Referenced to GND)	−0.5 to V_{CC}+0.5	V
I_{in}	DC Input Current, per Pin	±20	mA
I_{out}	DC Output Current, per Pin	±35	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	±75	mA
P_D	Power Dissipation in Still Air, Plastic or Ceramic DIP†	750	mW
	SOIC Package†	500	
T_{stg}	Storage Temperature	−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		°C
	(Plastic DIP or SOIC Package)	260	
	(Ceramic DIP)	300	

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND ≤ (V_{in} or V_{out}) ≤ V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

*Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — Plastic DIP: −10 mW/°C from 65° to 125°C
Ceramic DIP: −10 mW/°C from 100° to 125°C
SOIC Package: −7 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 4.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)		2.0	6.0	V
V_{in}, V_{out}	DC Input Voltage, Output Voltage (Referenced to GND)		0	V_{CC}	V
T_A	Operating Temperature, All Package Types		−55	+125	°C
t_r, t_f	Input Rise and Fall Time	V_{CC} = 2.0 V	0	1000	ns
	(Figure 1)	V_{CC} = 4.5 V	0	500	
		V_{CC} = 6.0 V	0	400	

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V_{CC} V	Guaranteed Limit			Unit
				25°C to −55°C	≤85°C	≤125°C	
V_{IH}	Minimum High-Level Input Voltage	V_{out} = V_{CC} − 0.1 V, $\|I_{out}\|$ ≤ 20 μA	2.0	1.5	1.5	1.5	V
			4.5	3.15	3.15	3.15	
			6.0	4.2	4.2	4.2	
V_{IL}	Maximum Low-Level Input Voltage	V_{out} = 0.1 V, $\|I_{out}\|$ ≤ 20 μA	2.0	0.3	0.3	0.3	V
			4.5	0.9	0.9	0.9	
			6.0	1.2	1.2	1.2	
V_{OH}	Minimum High-Level Output Voltage	V_{in} = V_{IH}, $\|I_{out}\|$ ≤ 20 μA	2.0	1.9	1.9	1.9	V
			4.5	4.4	4.4	4.4	
			6.0	5.9	5.9	5.9	
		V_{in} = V_{IH}, $\|I_{out}\|$ ≤ 6.0 mA	4.5	3.98	3.84	3.70	
		V_{in} = V_{IH}, $\|I_{out}\|$ ≤ 7.8 mA	6.0	5.48	5.34	5.20	
V_{OL}	Maximum Low-Level Output Voltage	V_{in} = V_{IL}, $\|I_{out}\|$ ≤ 20 μA	2.0	0.1	0.1	0.1	V
			4.5	0.1	0.1	0.1	
			6.0	0.1	0.1	0.1	
		V_{in} = V_{IL}, $\|I_{out}\|$ ≤ 6.0 mA	4.5	0.26	0.33	0.40	
		V_{in} = V_{IL}, $\|I_{out}\|$ ≤ 7.8 mA	6.0	0.26	0.33	0.40	
I_{in}	Maximum Input Leakage Current	V_{in} = V_{CC} or GND	6.0	±0.1	±1.0	±1.0	μA
I_{OZ}	Maximum Three-State Leakage Current	Output in High-Impedance State, V_{in} = V_{IL} or V_{IH}, V_{out} = V_{CC} or GND	6.0	±0.5	±5.0	±10.0	μA
I_{CC}	Maximum Quiescent Supply Current (per Package)	V_{in} = V_{CC} or GND, I_{out} = 0 μA	6.0	8	80	160	μA

NOTE: Information on typical parametric values can be found in Chapter 4.

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AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input $t_r = t_f$ = 6 ns)

Symbol	Parameter	V_{CC} V	Guaranteed Limit			Unit
			25°C to −55°C	≤85°C	≤125°C	
t_{PLH}, t_{PHL}	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 3)	2.0 4.5 6.0	120 24 20	150 30 26	180 36 31	ns
t_{PLZ}, t_{PHZ}	Maximum Propagation Delay, Output Enable to Output Y (Figures 2 and 4)	2.0 4.5 6.0	175 35 30	220 44 37	265 53 45	ns
t_{PZL}, t_{PZH}	Maximum Propagation Delay, Output Enable to Output Y (Figures 2 and 4)	2.0 4.5 6.0	190 38 32	240 48 41	285 57 48	ns
t_{TLH}, t_{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 3)	2.0 4.5 6.0	60 12 10	75 15 13	90 18 15	ns
C_{in}	Maximum Input Capacitance	—	10	10	10	pF
C_{out}	Maximum Three-State Output Capacitance (Output in High-Impedance State)	—	15	15	15	pF

NOTES:
1. For propagation delays with loads other than 50 pF, see Chapter 4.
2. Information on typical parametric values can be found in Chapter 4.

C_{PD}	Power Dissipation Capacitance (Per Buffer) Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ For load considerations, see Chapter 4.	Typical @ 25°C, V_{CC} = 5.0 V 40	pF

SWITCHING WAVEFORMS

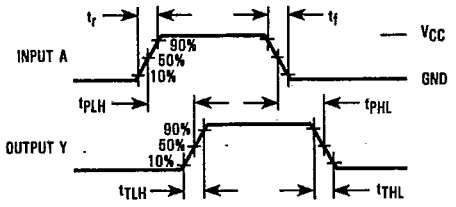


Figure 1

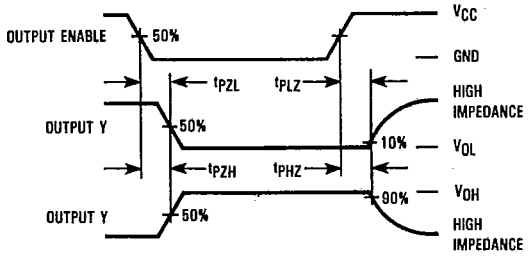
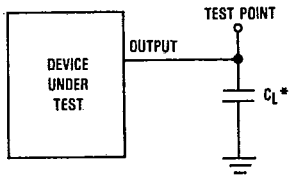
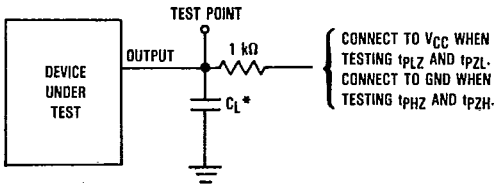


Figure 2



*Includes all probe and jig capacitance.

Figure 3. Test Circuit

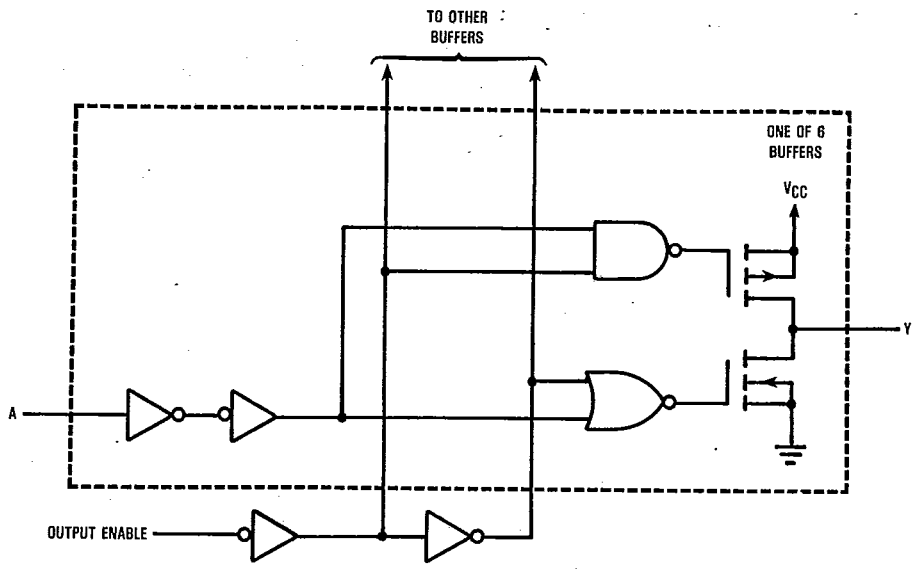


*Includes all probe and jig capacitance.

Figure 4. Test Circuit

MC54/74HC367

LOGIC DETAIL



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